

10/541583

JC14 Re PCT/PTO 07 JUL 2005
PATENT
8074-1061

IN THE U.S. PATENT AND TRADEMARK OFFICE

In re application of

Yasuhiro OKAMOTO et al.

Conf.

Application No. NEW NATIONAL PHASE

Group

Filed July 7, 2005

Examiner

FIELD-EFFECT TRANSISTOR

INFORMATION DISCLOSURE STATEMENT
(SUBMISSION CONCURRENT WITH THE
FILING OF A NEW PATENT APPLICATION)

Assistant Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

July 7, 2005

Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, and in fulfillment of the duty of disclosure under 37 C.F.R. § 1.56, applicant(s) hereby submit(s) an Information Disclosure Statement for consideration by the Examiner.

I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION

The patents, publications, or other information submitted for consideration by the Office are listed on PTO-1449, attached hereto.

II. COPIES

- Copies of the U.S. patents or publications are not submitted since the USPTO has waived their submission for applications filed after June 30, 2003.
- Submitted herewith is a legible copy of (i) each foreign patent; (ii) each publication or that portion which caused it to be listed; and (iii) all other information or that portion which caused it to be listed.
- This application is a National Phase of a PCT application. Some or all of the documents listed on the PTO-1449 are not enclosed because they were cited in the International Search Report and copies should have been forwarded from the International Search Authority pursuant to the trilateral agreement between the USPTO, EPO and JPO, or they are U.S. patents or U.S. published applications. If copies are needed, please contact the undersigned.

III. CONCISE EXPLANATION OF THE RELEVANCE
(check at least one box)

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a. DOCUMENTS IN THE ENGLISH LANGUAGE

The attached non U.S. patents, non U.S. patent application publications, foreign publications, or other information in the English language do not require a statement of relevancy.

b. DOCUMENTS NOT IN THE ENGLISH LANGUAGE

A concise explanation of the relevance of all patents, publications, or other information listed that is not in the English language is as follows:

Abstracts are provided.

c. FOREIGN SEARCH REPORT OR ACTION

An English language version of the search report or action that indicates the degree of relevance found by the foreign office is attached, thereby satisfying the requirement for a concise explanation. See MPEP 609(A)(3).

d. OTHER

The following additional information is provided for the Examiner's consideration.

FEES

This Information Disclosure Statement is being filed concurrently with the filing of a new patent application; therefore, no fee is required.

If The Examiner has any questions concerning this IDS, he/she is requested to contact the undersigned.

Respectfully submitted,

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Enclosures: Form PTO-1449(s)
 Documents
 Foreign Search Report
 Other: _____

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		Attorney Docket No.: 8074-1061	Application No. 10/1541583 NEW NATIONAL PHASE			
		Applicant: Yasuhiro OKAMOTO et al.	Filing Date: July 7, 2005	Group Art Unit:		
U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	
Filing date (if appropriate)						
FOREIGN PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation
	JP 2000-286428	10/13/2000	JAPAN			Yes
	JP 11-176839	7/2/1999	JAPAN			No
	JP 2002-359256	12/13/2002	JAPAN			
	JP 2001-189324	7/10/2001	JAPAN			
	JP 2002-222860	8/9/2002	JAPAN			
	JP 2000-003919	1/7/2000	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
	U. K. MISHRA et al., "AlGaN/GaN HEMTs-An Overview of Device Operation and Applications", Proceedings of the IEEE, Vol. 90, No. 6, June 2002					
	J. LI et al., "High breakdown voltage GaN HFET with field plate", ELECTRONICS LETTERS, 1 st February 2001, Vol. 37, No. 3					
	Y. ANDO et al., "A 110-W AlGaN/GaN HETEROJUNCTION FET ON THINNED SAPPHIRE SUBSTRATE"					
EXAMINER:			DATE CONSIDERED			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						

* English language abstract provided for the Examiner's convenience